

**TECHNICAL DATA**  
**DATA SHEET 330, REV. A****ULTRA LOW REVERSE LEAKAGE POWER SCHOTTKY RECTIFIER**  
**Very Low Voltage Drop****DESCRIPTION:** 200 VOLT, 3.0 AMP, POWER SCHOTTKY RECTIFIER IN A HERMETIC SHD-1/A/B PACKAGE.**MAXIMUM RATINGS**ALL RATINGS ARE @  $T_C = 25^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	200	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ $T_C=100^\circ\text{C}$ )	$I_O$	3.0	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT ( $t = 8.3\text{ms}$ , Sine)	$I_{FSM}$	55	Amps
MAXIMUM JUNCTION CAPACITANCE ( $V_r=5\text{V}$ ) (per leg)	$C_T$	60	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R\theta_{JC}$	3.7	$^\circ\text{C/W}$
MAXIMUM OPERATING TEMPERATURE RANGE	$T_{op}$	-65 to + 200	$^\circ\text{C}$
MAXIMUM STORAGE TEMPERATURE RANGE	$T_{stg}$	-65 to + 175	$^\circ\text{C}$

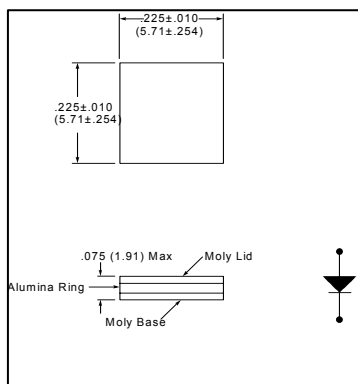
**ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC			
MAXIMUM FORWARD VOLTAGE DROP, Pulsed ( $I_f = 3.0\text{ Amps}$ ) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	$V_f$	0.92 0.76	Volts
MAXIMUM REVERSE CURRENT ( $I_r$ @ 200V PIV) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	$I_r$	0.003 0.2	mA
REVERSE RECOVERY TIME	$t_{rr}$	9	ns

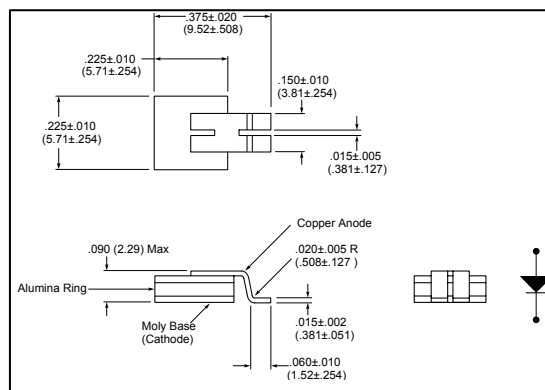
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**MECHANICAL DIMENSIONS: In Inches / mm**

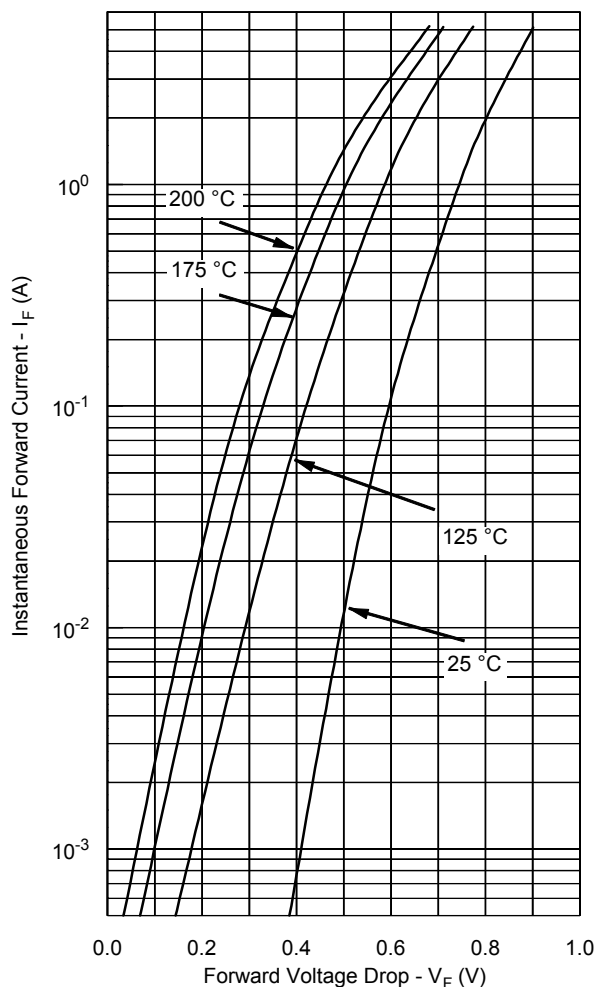
**SHD-1**



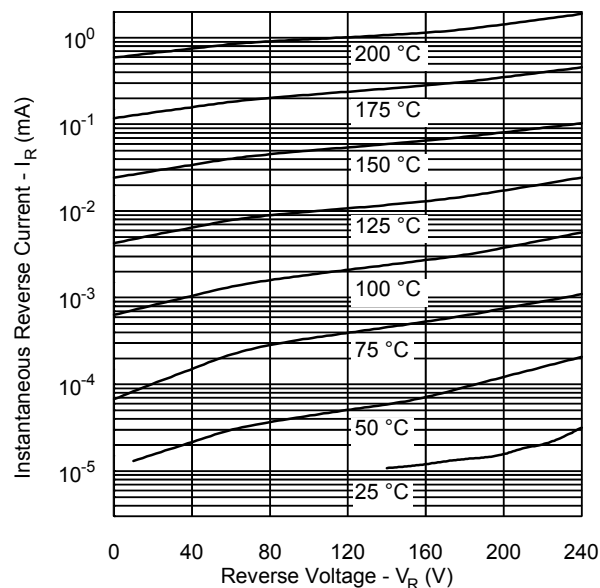
**SHD-1B**



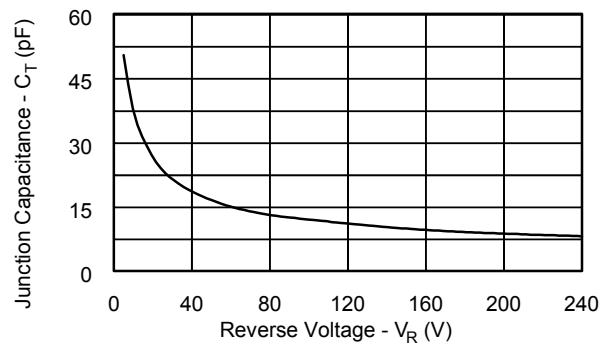
**Typical Forward Characteristics**



**Typical Reverse Characteristics**



**Typical Junction Capacitance**



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